

## Supporting Information

# Low-pressure Accessible Gas-quenching for Absolute Methylammonium-free Perovskite Solar Cells

Tian Hou<sup>a</sup>, Meng Zhang<sup>\*a,b,d</sup>, Wenjing Yu<sup>a</sup>, Xin Wang<sup>a</sup>, Zhengying Gu<sup>c</sup>, Qian Chen<sup>a</sup>, Lan Lan<sup>a</sup>, Xiaoran Sun<sup>\*a</sup>, Yuelong Huang<sup>\*a,b</sup>, Bolin Zheng<sup>d</sup>, Xu Liu<sup>d</sup>, Martin A. Green<sup>d</sup>, Xiaojing Hao<sup>\*d</sup>

a. Institute of Photovoltaics, Southwest Petroleum University, Chengdu 610500, China

b. State Key Laboratory of Oil and Gas Reservoir Geology and Exploitation, Southwest Petroleum University, Chengdu, 610500, China

c. School of Chemistry and Molecular Engineering, East China Normal University, Shanghai 200241, China

d. The Australian Centre for Advanced Photovoltaics, School of Photovoltaic and Renewable Energy Engineering, University of New South Wales, Sydney, NSW 2052, Australia

## Figures

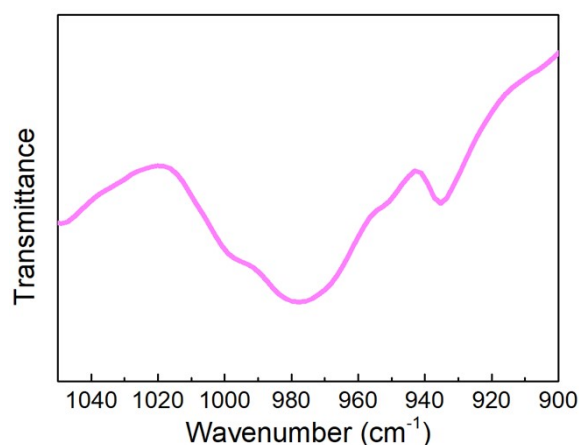


Fig. S1. The FTIR spectra of the 1 hour aged intermediate film with gas-quenching.

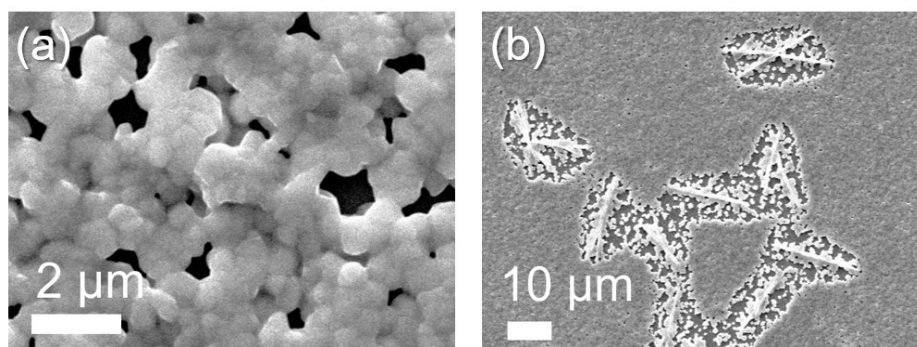


Fig. S2. (a) SEM topography of the  $\text{FA}_{0.9}\text{Cs}_{0.1}\text{PbI}_3$  film prepared without gas-quenching. (b) SEM topography of gas-quenched the  $\text{FA}_{0.9}\text{Cs}_{0.1}\text{PbI}_3$  film with annealing of 1 hour delayed.

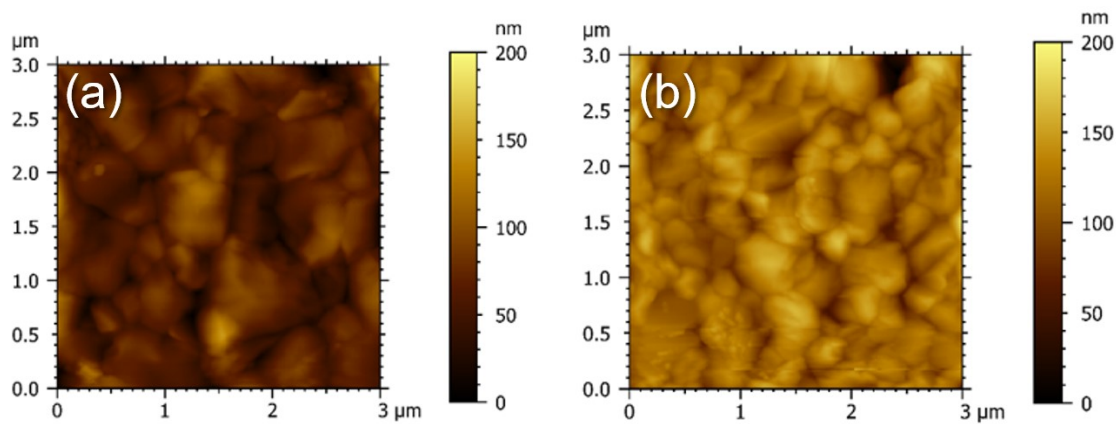


Fig. S3. AFM topography of gas-quenched the  $\text{FA}_{0.9}\text{Cs}_{0.1}\text{PbI}_3$  film with (a) TMSO and (b) DMSO.

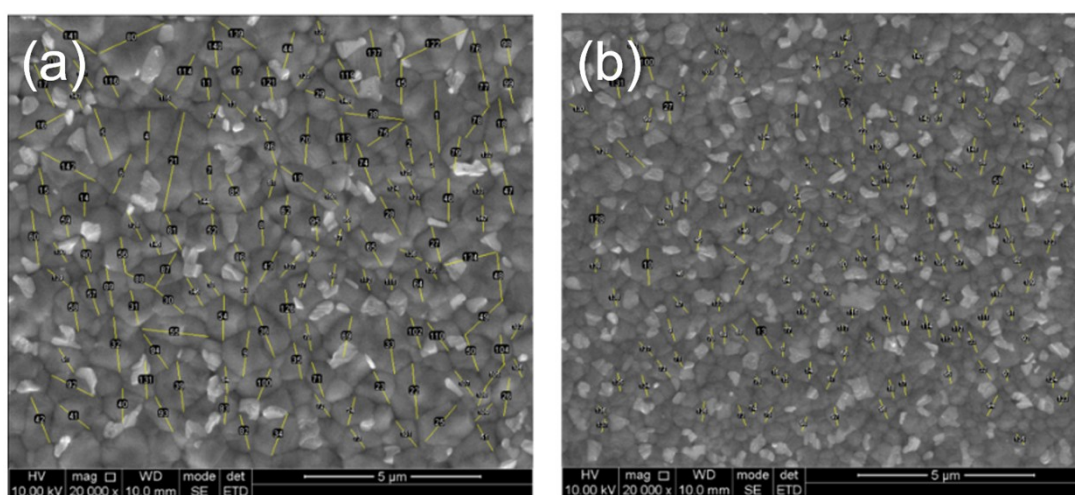


Fig. S4. SEM images for grain-size analysis of gas-quenched the  $\text{FA}_{0.9}\text{Cs}_{0.1}\text{PbI}_3$  film with (a) TMSO and (b) DMSO.

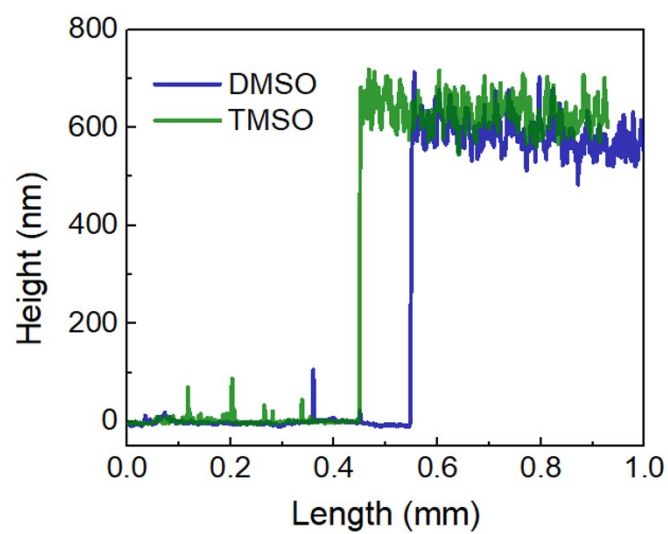


Fig. S5. Thickness profile of perovskite films prepared with DMSO and TMSO.

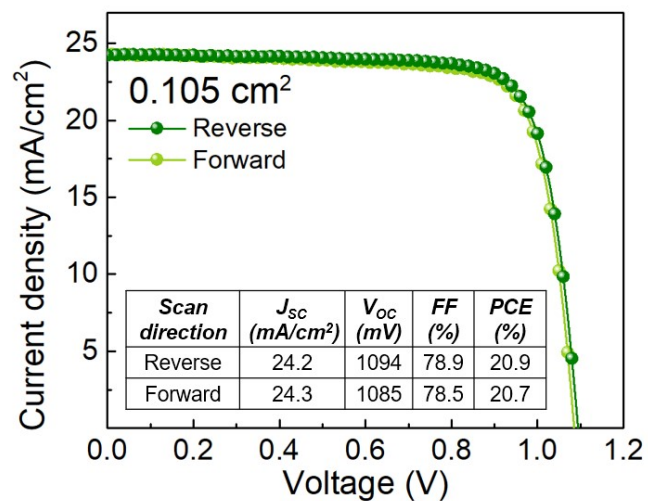


Fig. S6. Bidirectional J-V curves of the TMSO device with highest  $V_{oc}$ .

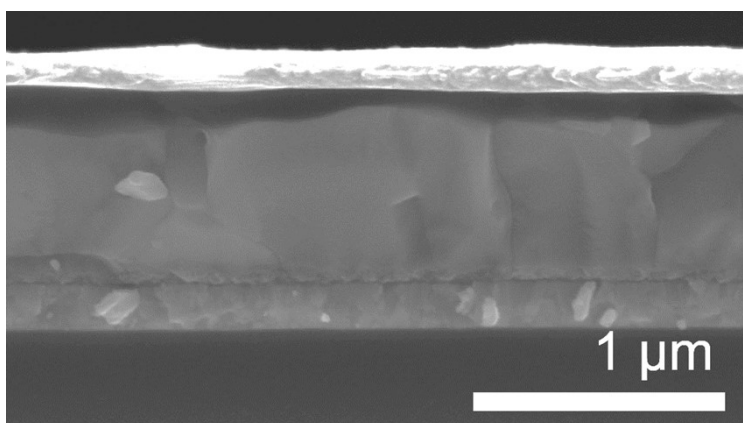


Fig. S7. Cross-sectional SEM image of ITO/SnO<sub>2</sub>/FA<sub>0.9</sub>Cs<sub>0.1</sub>PbI<sub>3</sub>/spiro-OMeTAD/Ag device

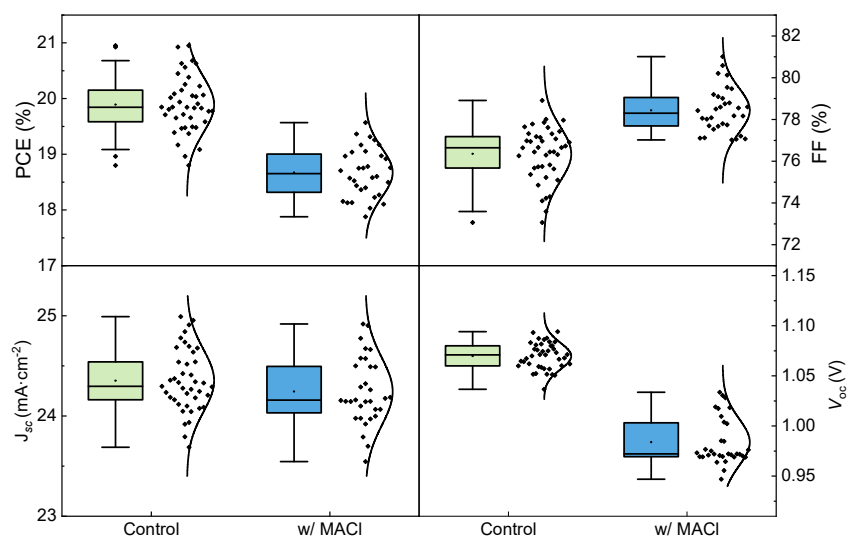


Fig. S8. Statistical photovoltaic parameters of PSCs prepared with and without MACl (0.2M added in precursor).

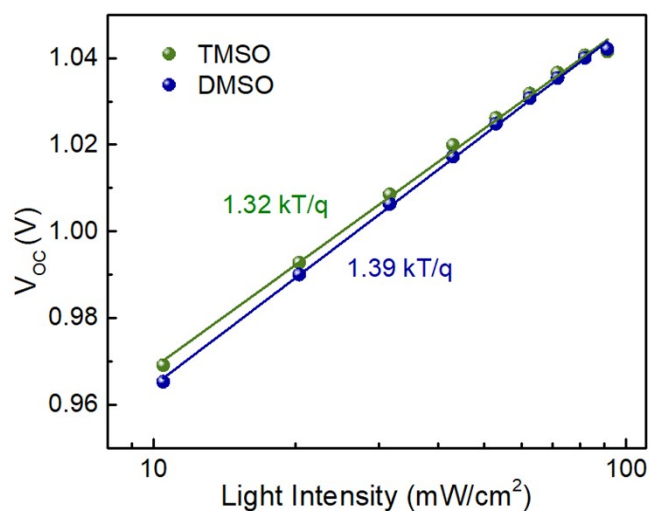


Fig. S9.  $V_{oc}$  versus light intensity curves for the PSCs process with TMSO and DMSO

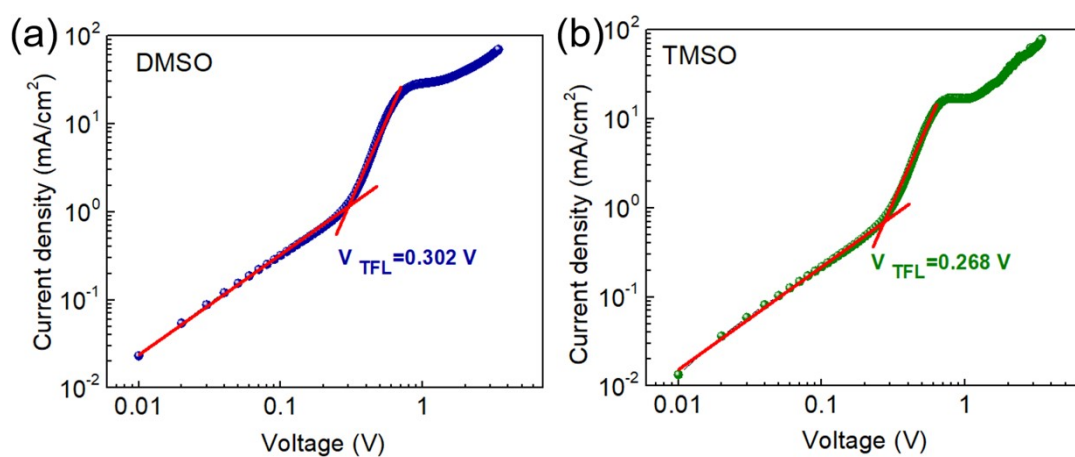


Fig. S10. J-V characteristics of the (a) DMSO sample and (b) TMSO sample from the SCLC measurements of the device structured with ITO/PEDOT:PSS/perovskite/spiro-OMeTAD/Ag ( $V_{TFL}$ , trap-filled limited voltage).

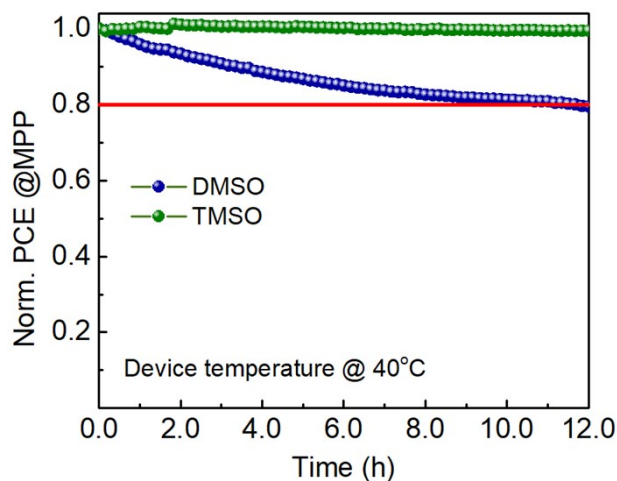


Fig. S11. MPP tracking (in  $N_2$ ) of unencapsulated device prepared with TMSO and DMSO

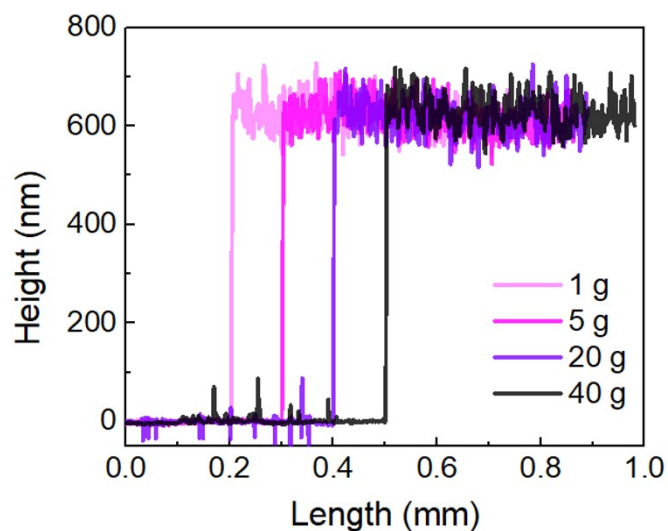


Fig. S12. Thickness profile of perovskite films prepared under different gas-pressure

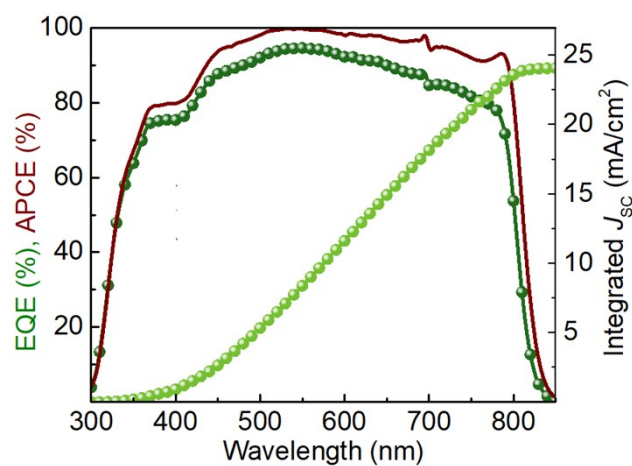


Fig. S13. EQE and APCE spectrum of the gas-quenched device fabricated with TMSO.

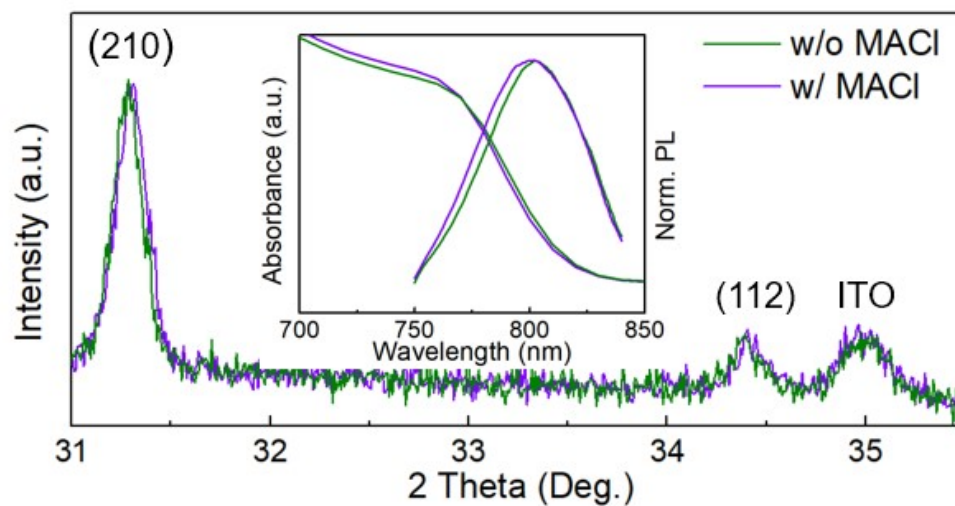


Fig. S14. XRD patterns of the  $\text{FA}_{0.9}\text{Cs}_{0.1}\text{PbI}_3$  films with and without the additive of MACl; inset: Light absorption spectra and steady-state PL spectra of the samples.

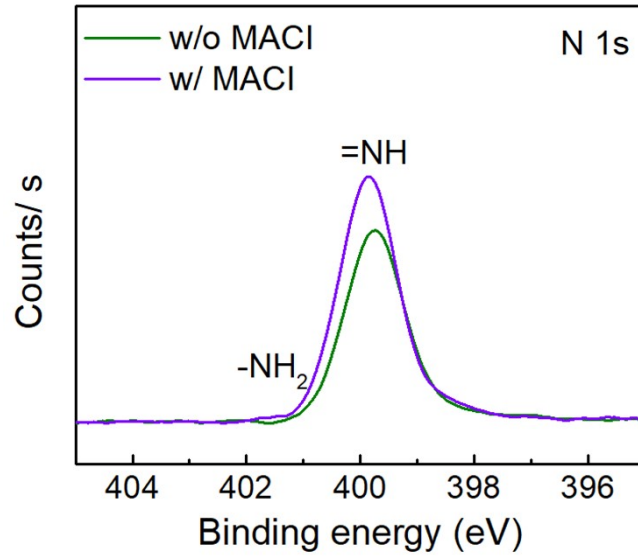


Fig. S15. N 1s XPS spectra of the  $\text{FA}_{0.9}\text{Cs}_{0.1}\text{PbI}_3$  films with and without the additive of MACI

## Tables

Table S1 Full width at half maxima (FWHM) of the XRD peaks in Fig. 3a

Peaks	DMSO-sample	TMSO-sample
(001)	0.243	0.152
(111)	0.339	0.289
(002)	0.302	0.175
(012)	0.358	0.214